DECLARATION FOR PATENT APPLICATION

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled TRANSISTOR

TRANSISTOR				
The specification of which is attached	hereto unless the follow	ving box is checked:		
☐ was filed on	as United States A	pplication Number	or PCT International	Application Numbe
and was amended on	(if applicab	le).		
I hereby state that I have reviewed at	nd understand the conte	nts of the above ide	ntified specification, in	cluding the claims, a
amended by any amendment referred	to above.			
I acknowledge the duty to disclose inf	ormation which is mater	rial to patentability a	s defined in 37 CFR §	1.56.
I hereby claim foreign priority benef	its under 35 U.S.C. §	119(a)-(d) or 365(t	o) of any foreign applic	ation(s) for patent o
inventor's certificate, or § 365(a) of	f any PCT International	application which o	lesignated at least one c	ountry other than the
United States, listed below and have a	lso identified below, by	checking the box, a	ny foreign application for	or patent or inventor'.
certificate, or PCT International applic				•
			·	riority Not Claimed
(Number)	(Country)	(Day/Month	/Vear Filed)	
	•		,	
(Number)	(Country)	(Day/Month	•	
I hereby claim the benefit under 35 U.	S.C. § 119(e) of any U	United States provision	onal application(s) listed	below.
(Application Number)		(Filing Date)		
(Application Number)	<u></u>	(Filing Date)		
I hereby claim the benefit under 35 U	S.C. § 120 of any Ur	ited States application	on(s), or § 365(c) of a	ny PCT Internationa
application designating the United Sta	tes, listed below and, in:	sofar as the subject n	natter of each of the clai	ms of this applicatior
is not disclosed in the prior United States. U.S.C. § 112.	ates or PCT Internationa	al application in the	manner provided by the	first paragraph of 35
I acknowledge the duty to disclose info	ormation which is mater	rial to patentability a	s patentability as define	d in 37 CFR § 1.56
which became available between the f				
application.				C
(Application Number)	(Filing Date	e)	(Status-patented, pend	ling abandoned)
(Application Number) I hereby appoint the following attorne	(Filing Date		(Status-patented, pend	· , .
	Welandlor agentlel to n			
and Trademark Office connected there	with: MORTON J. ROS	ENBERG, ESQ., RE	EG. #26,049; DAVID R	. WOOD, #53,86
and Trademark Office connected there	with: MORTON J. ROS DAVID I. KLEIN	ENBERG, ESQ., RE J, ESQ., REG. #33,2	EG. #26,049; DAV ID R 53; JUN Y. LEE, ESQ.,	. WOOD, #53,866 REG. #40,262
and Trademark Office connected there	with: MORTON J. ROS DAVID I. KLEIN	ENBERG, ESQ., RE I, ESQ., REG. #33,2 ENBERG at telepho	EG. #26,049; DAVID R	. WOOD, #53,86 REG.#40,262

Page 1

E-MAIL ADDRESS: rkl@rklpatlaw.com

ELLICOTT CITY, MD 21043

FAX #: 410-461-3067

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

					•	-	(CHANG	IS
Full name of sole or first inventor (given name, family name)						Ming-Hsuan CHANG	FAMILY	NAME)
Inventor's signature	>	Ming	- Hsuan	CHANG	g Date			
Citizenship Tair	wan R.O.C.	1						
Mailing Address	FL. 3, NO. 3	31, LANE	125, SEC. 4,	SAN-HO ROA	AD, SAN-CHUI	NG CITY, TAIPEI, TAI	WAN, R.O	.C.